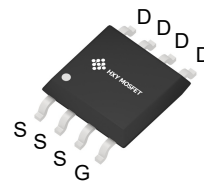




Description

The HXY4480S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



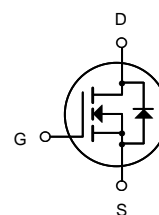
SOP-8

General Features

$V_{DS} = 40V$ $I_D = 14A$
 $R_{DS(ON)} < 18m\Omega$ @ $V_{GS}=10V$
 $R_{DS(ON)} < 24m\Omega$ @ $V_{GS}=4.5V$

Application

Battery protection
Load switch
Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY4480S	SOP-8	4480 XXXX	3000

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	14	A
$I_D (70^{\circ}C)$	Drain Current-Continuous($T_C=70^{\circ}C$)	10	A
I_{DM}	Pulsed Drain Current	70	A
P_D	Maximum Power Dissipation	3.1	W
E_{AS}	Single pulse avalanche energy (Note 5)	135	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}C$



Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DS}	$I_D=250\mu A$, $V_{GS}=0V$	40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=32V$, $V_{GS}=0V$			1	μA
		$V_{DS}=32V$, $V_{GS}=0V$, $T_J=55^\circ C$			5	
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0V$, $V_{GS}=\pm 20V$			± 100	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$	1		3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$, $I_D=14A$		14	18	$m\Omega$
		$V_{GS}=10V$, $I_D=14A$, $T_J=125^\circ C$		18	24	
		$V_{GS}=4.5V$, $I_D=5A$			16.5	
On State Drain Current	$I_{D(on)}$	$V_{GS}=10V$, $V_{DS}=5V$	70			A
Forward Transconductance	g_{FS}	$V_{DS}=5V$, $I_D=5A$	50			S
Input Capacitance	C_{iss}	$V_{GS}=0V$, $V_{DS}=20V$, $f=1MHz$		1600	1920	pF
Output Capacitance	C_{oss}			320		
Reverse Transfer Capacitance	C_{rss}			100		
Gate Resistance	R_g	$V_{GS}=0V$, $V_{DS}=0V$, $f=1MHz$		3.4		Ω
Total Gate Charge (10V)	Q_g	$V_{GS}=10V$, $V_{DS}=20V$, $I_D=14A$		22		nC
Total Gate Charge (4.5V)				10.5		
Gate Source Charge				4.2		
Gate Drain Charge				4.8		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS}=10V$, $V_{DS}=20V$, $R_L=1.5\Omega$, $R_{GEN}=3\Omega$		3.5		ns
Turn-On Rise Time	t_r			6		
Turn-Off DelayTime	$t_{d(off)}$			13.2		
Turn-Off Fall Time	t_f			3.5		
Body Diode Reverse Recovery Time	t_{rr}	$I_F=14A$, $dI/dt=100A/\mu s$		31		nC
Body Diode Reverse Recovery Charge	Q_{rr}			33		
Maximum Body-Diode Continuous Current	I_S				4	A
Diode Forward Voltage	V_{SD}	$I_S=1A$, $V_{GS}=0V$			1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.



Typical Characteristics

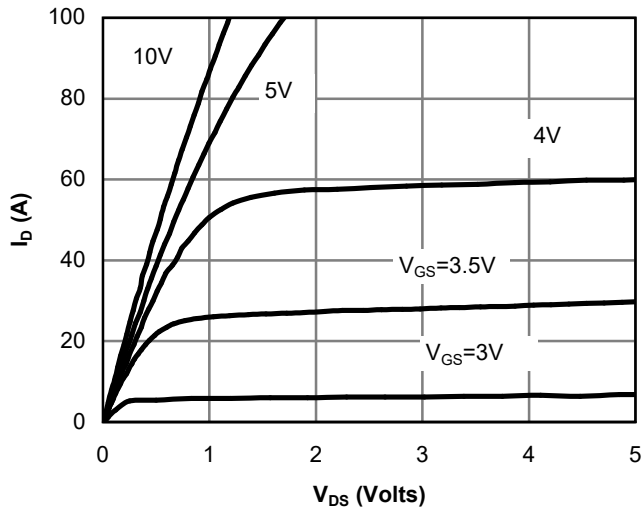


Figure 1: On-Region Characteristics

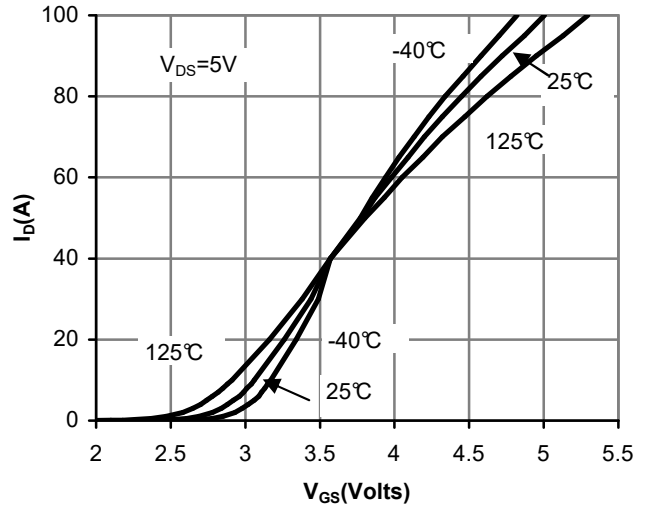


Figure 2: Transfer Characteristics

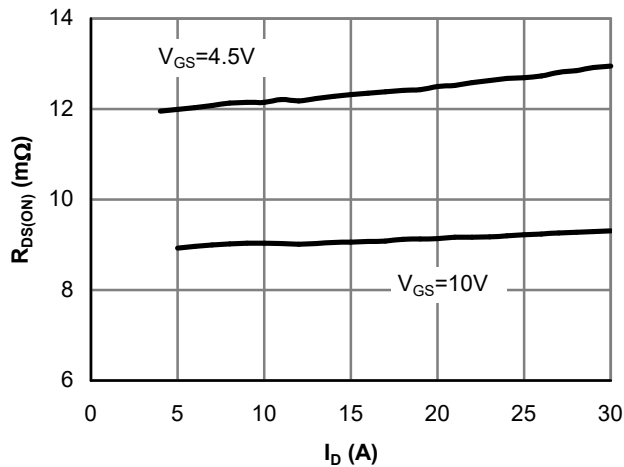


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

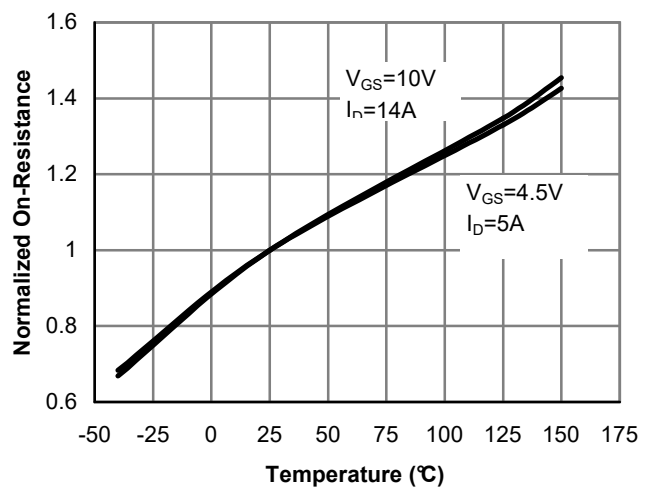


Figure 4: On-Resistance vs. Junction Temperature

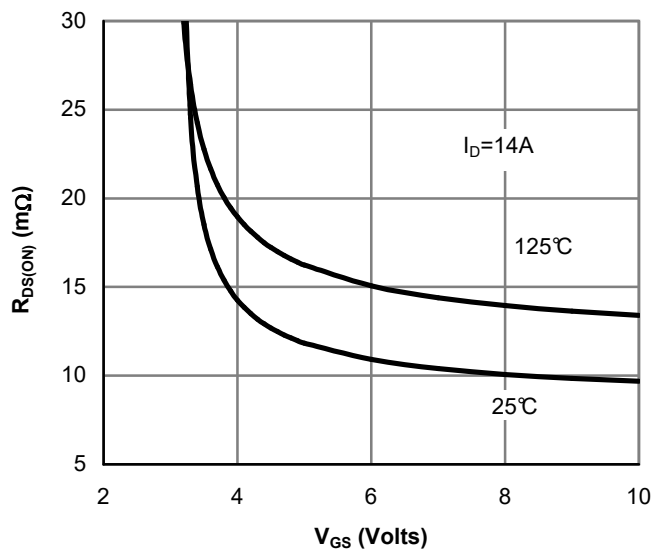


Figure 5: On-Resistance vs. Gate-Source Voltage

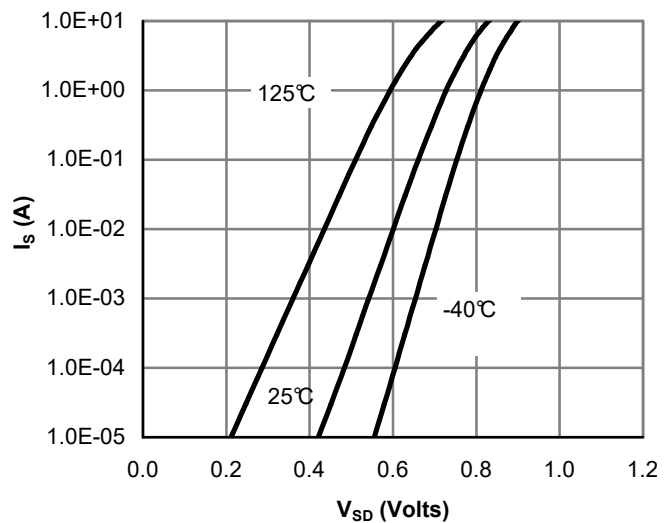


Figure 6: Body-Diode Characteristics

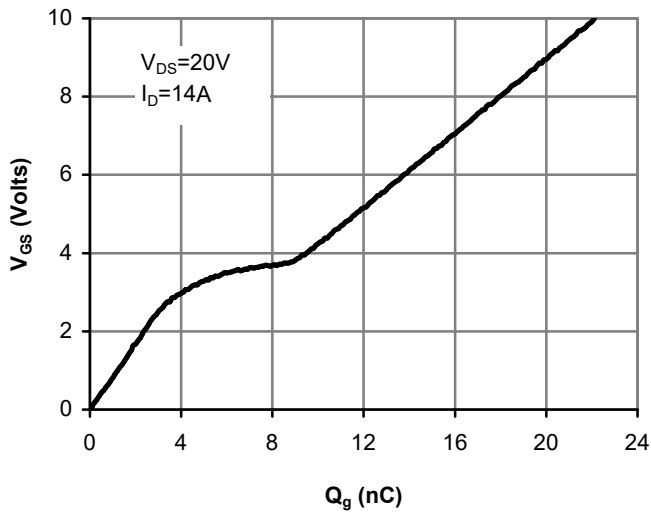


Figure 7: Gate-Charge Characteristics

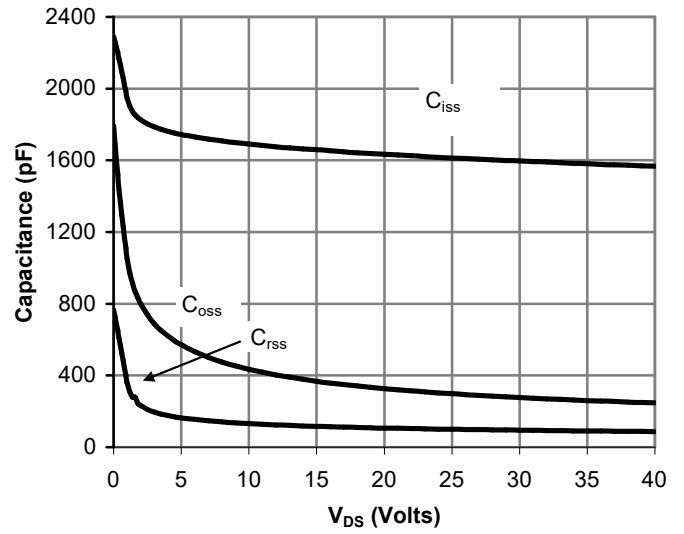


Figure 8: Capacitance Characteristics

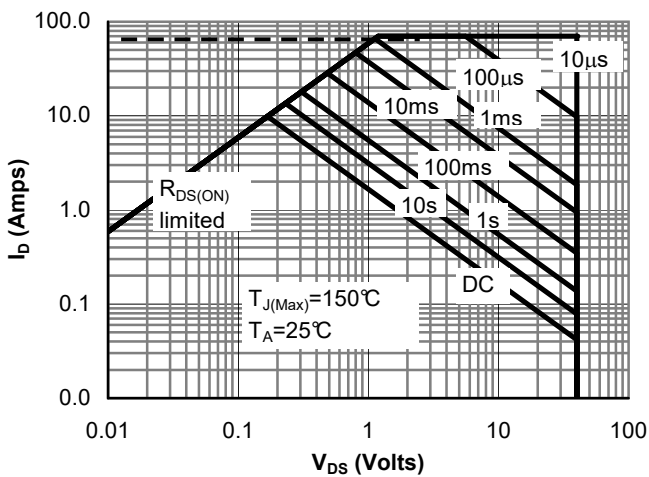


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

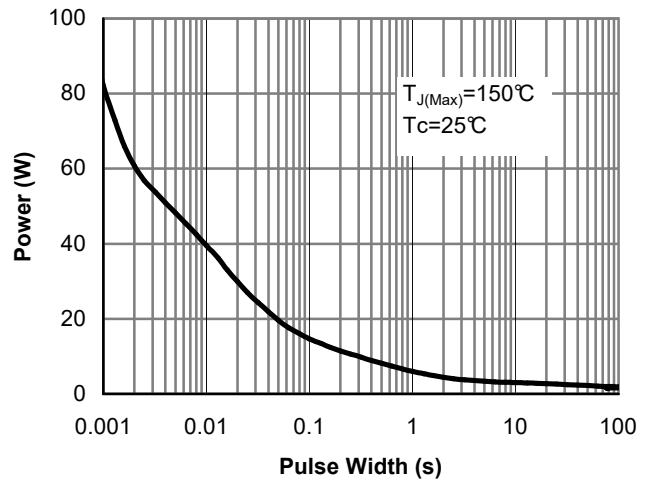


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

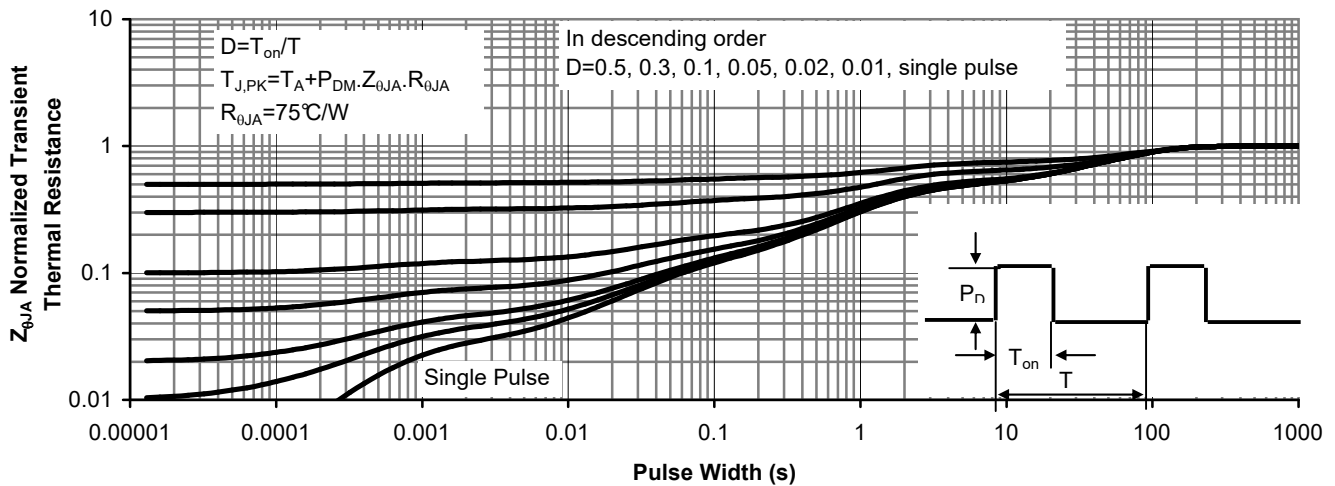
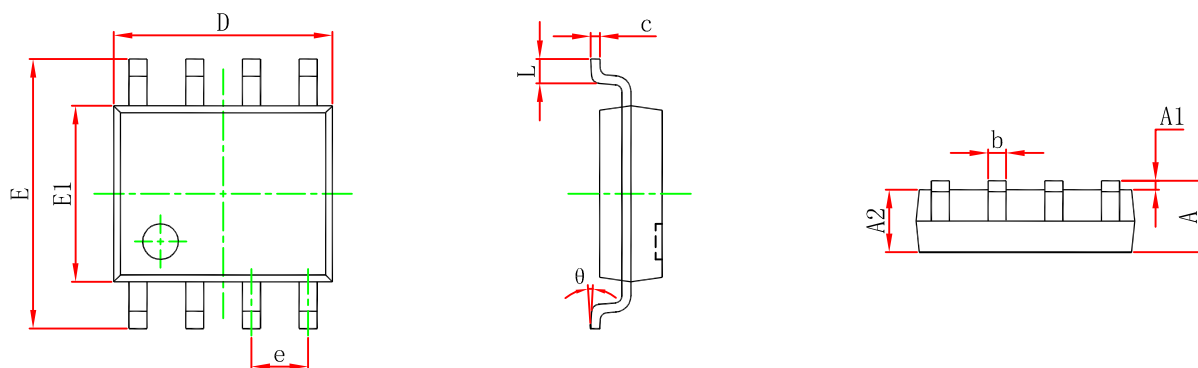


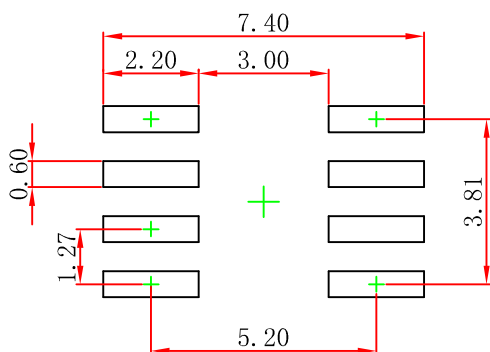
Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)



SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:
1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.



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